

N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY $V_{DS}(V)$ Q_g (Typ.) $R_{DS(on)}(m\Omega)(Typ.)$ I_D (A)^a 1.6 at V_{GS}= 10 V 40 135 52 nC $2.8 \text{ at } V_{GS} = 4.5 \text{ V}$

Din-Tek

FEATURES

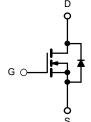
- DT-Trench Power MOSFET
- · Improved dv/dt Capability
- Fast switching
- Green Device Available

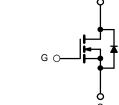
APPLICATIONS

- Motor Drive
- Power Tools
- · LED Lighting
- · Quick Charger

DFN3.3X3.3-8L Pin Configuration

Top View





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25 ^{\circ}C$, unless othe	rwise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	40	V
Gate-Source Voltage		V _{GS}	± 20	V
Continuous Darin Courset /T 450 90\2	T _C = 25 °C	,	135	
Continuous Drain Current (T _J = 150 °C) ^a	T _C = 100 °C	I _D	99	А
Pulsed Drain Current ^b		I _{DM}	520	
Single Avalanche Energy		E _{AS}	259	mJ
Mariana Bana Biadadia	T _C = 25 °C	D	95	W
Maximum Power Dissipation ^c	T _C = 100 °C		P _D 38	
Operating Junction and Storage Temperature Ra	ange	T _J , T _{stg}	- 55 to +150	°C

8 D 7 D

6 D

5 D

S [2

G

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) ^d	R _{thJA}	62	°C/W		
Junction-to-Case (Drain)	R _{thJC}	1.3]		

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of Reja is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with Ta=25 °C.



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	40	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.2	-	2.5		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	μΑ	
Zana Cata Valtana Basis Commet	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V	-	-	1	μА	
Zero Gate Voltage Drain Current		V _{DS} = 32 V, V _{GS} = 0 V, T _J = 100 °C	-	-	10		
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	135	-	-	Α	
Drain Source On State Registered 8	Б	V _{GS} = 10 V, I _D = 20 A	-	1.6	2.05	mΩ	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 15 A	-	2.8	3.6		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 10 \text{ V}, I_D = 3 \text{ A}$	-	15	-	S	
Dynamic ^b				<u> </u>			
Input Capacitance	C _{iss}		-	2950	-	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$	-	1100	-		
Reverse Transfer Capacitance	C _{rss}		-	58	-		
Total Gate Charge ^c	Q_g		-	52	-	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 65 \text{ A}$	-	8.3	-		
Gate-Drain Charge ^c	Q_{gd}		-	14	-		
Gate Resistance	Rg	f = 1 MHz	-	0.9	-	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	10	-		
Rise Time ^c	t _r	$V_{DD} = 20 \text{ V}, I_D = 65 \text{ A}, R_g = 6 \Omega$	-	15	-	ns	
Turn-Off Delay Time ^c	t _{d(off)}	V _{GS} = 10 V	-	20	-		
Fall Time ^c	t _f		-	30	-		
Drain-Source Body Diode Ratings and	Characterist	ics ^b (T _C = 25 °C)		•	,		
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	135	Α	
Pulsed Current	I _{SM}		-	-	520	Α	
Forward Voltage ^a	V _{SD}	I _F = 1 A, V _{GS} = 0 V	-	-	1	V	
Reverse Recovery Time	t _{rr}	L = 10 A di/dt = 100 A/us	-	70	-	ns	
Reverse Recovery Charge	Q_{rr}	$I_F = 10 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	100	-	nC	

Notes

- a. Pulse test; pulse width \leq 200 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (25°C, unless otherwise noted)

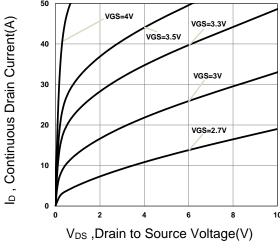


Fig.1 Typical Output Characteristics

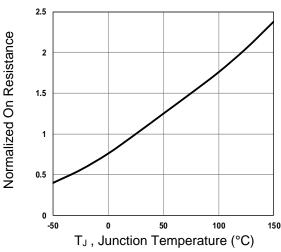


Fig. 3 Normalized RDSON vs. T_J

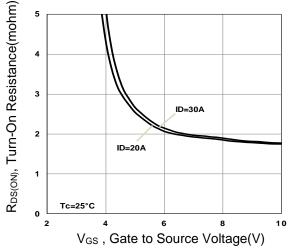


Fig. 5 Turn-On Resistance vs. V_{GS}

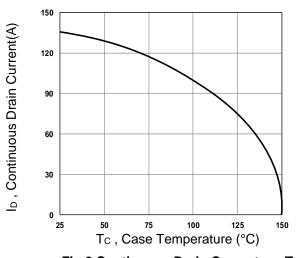


Fig.2 Continuous Drain Current vs. $T_{\rm C}$

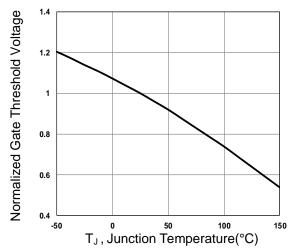


Fig. 4 Normalized V_{th} vs. T_J

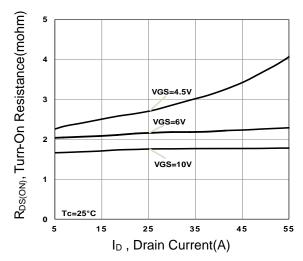


Fig. 6 Turn-On Resistance vs. ID



TYPICAL CHARACTERISTICS (25°C, unless otherwise noted)

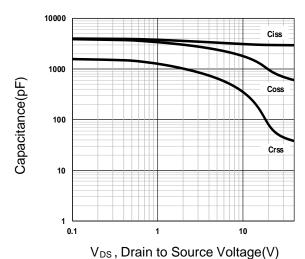


Fig. 7 Capacitance Characteristics

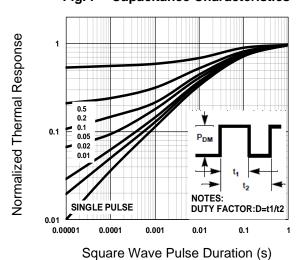


Fig. 9 Normalized Transient Impedance

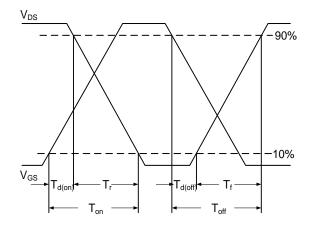


Fig. 11 Switching Time Waveform

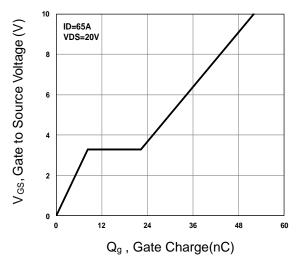


Fig. 8 Gate Charge Characteristics

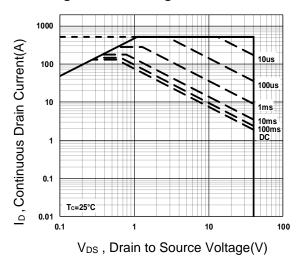


Fig. 10 Maximum Safe Operation Area

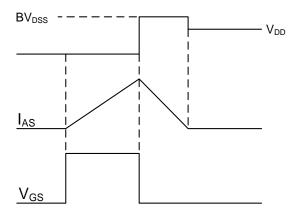
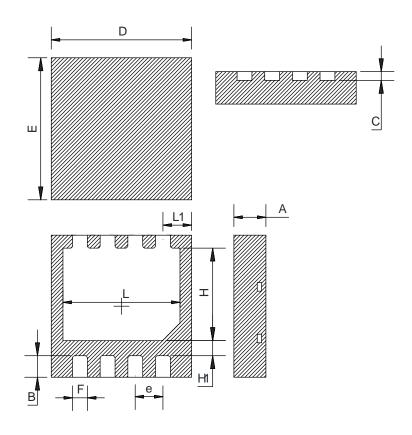


Fig. 12 EAS Waveform



DFN3.3X3.3-8L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max
А	0.60	0.75	0.90
В	0.30	0.50	0.70
С	0.143	0.203	0.263
D	3.15	3.30	3.45
Е	3.15	3.30	3.45
е	0.50	0.65	0.80
F	0.25	0.35	0.45
Н	1.85	2.15	2.45
H1	0.20	0.35	0.50
L	2.35	2.75	3.15
L1	0.475	0.675	0.875





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